

30V N-Channel Enhancement Mode Mosfet

Voltage 30 V Current 10 A

Features

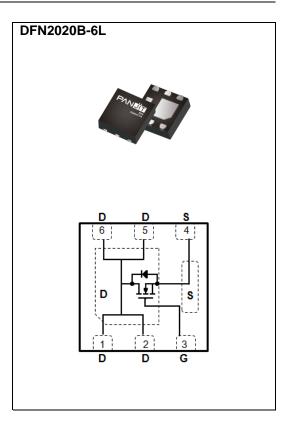
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@5A<12m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@3A<18m\Omega$
- High switching speed
- Improved dv/dt capability
- Low gate charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN2020B-6L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0086 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | | SYMBOL | LIMIT | UNITS | |
|--|----------------------|-----------------|-------------|-------|--|
| Drain-Source Voltage | | V _{DS} | 30 | V | |
| Gate-Source Voltage | | V _{GS} | <u>+</u> 20 | | |
| Continuous Drain Current(Note 4) | | I _D | 10 | A | |
| Pulsed Drain Current ^(Note 1) | | I _{DM} | 40 | | |
| Power Dissipation | T _A =25°C | P _D | 2 | W | |
| | Derate above 25°C | | 16 | mW/°C | |
| Operating Junction and Storage Temperature Range | | TJ,TSTG | -55~150 | °C | |
| Typical Thermal Resistance - Junction to Ambient ^(Note 4,5) | | Reja | 62.5 | °C/W | |



Electrical Characteristics (T_A=25°C unless otherwise noted)

| PARAMETER | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNITS | |
|----------------------------------|--|--|------|------|--------------|-------|--|
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} V _{GS} =0V, I _D =250uA | | 30 | - | - | V | |
| Gate Threshold Voltage | $V_{GS(th)}$ | V _{DS} =V _{GS} , I _D =250uA | 1 | 1.53 | 2.5 | V | |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V, I _D =5A | - | 9.7 | 12 | mΩ | |
| | | V _{GS} =4.5V, I _D =3A | - | 13 | 18 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V, V _{GS} =0V | - | - | 1 | uA | |
| Gate-Source Leakage Current | Igss | V _{GS} = <u>+</u> 20V, V _{DS} =0V | - | - | <u>+</u> 100 | nA | |
| Dynamic ^(Note 6) | | | | | | | |
| Total Gate Charge | Q_g | \/ A5\/ 5A | - | 7.1 | - | nC | |
| Gate-Source Charge | Qgs | V _{DS} =15V, I _D =5A, V _{GS} =4.5V ^(Note 2,3) | - | 2 | - | | |
| Gate-Drain Charge | Q_{gd} | VGS=4.5 V(10.60 2,0) | - | 2.8 | - | | |
| Input Capacitance | Ciss | | - | 660 | - | pF | |
| Output Capacitance | Coss | V _{DS} =25V, V _{GS} =0V, f=1MHZ | - | 92 | - | | |
| Reverse Transfer Capacitance | Crss | I=IIVIMZ | - | 71 | - | | |
| Turn-On Delay Time | td _(on) | | - | 6.7 | - | ns | |
| Turn-On Rise Time | tr | V _{DD} =15V, I _D =1A, | - | 11 | - | | |
| Turn-Off Delay Time | td _(off) | $V_{GS}=10V, R_{G}=6\Omega$ (Note 2,3) | - | 27 | - | | |
| Turn-Off Fall Time | tf | (************************************** | - | 8.3 | - | | |
| Drain-Source Diode | | | | | | | |
| Maximum Continuous Drain-Source | Is | | - | - | 1.5 | А | |
| Diode Forward Current | 15 | | | | | | |
| Diode Forward Voltage | V_{SD} | I _S =1A, V _{GS} =0V | - | 0.71 | 1 | V | |

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. Roja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

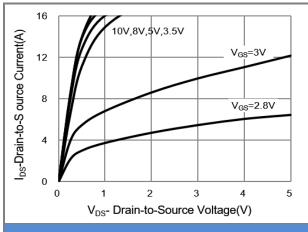


Fig.1 On-Region Characteristics

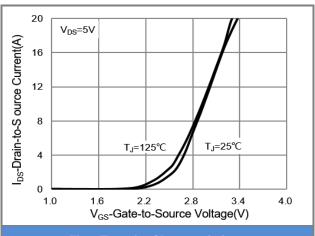


Fig.2 Transfer Characteristics

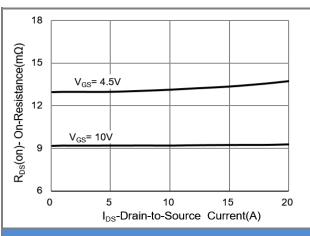


Fig.3 On-Resistance vs. Drain Current

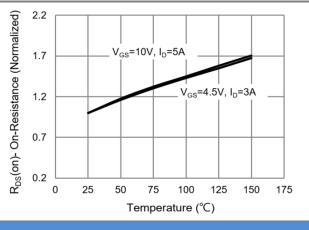
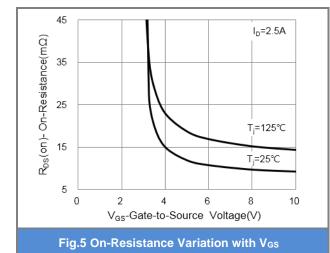
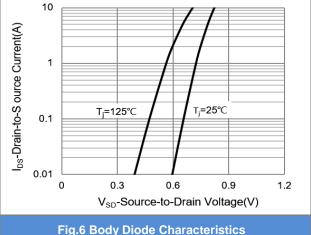


Fig.4 On-Resistance vs. Junction temperature







TYPICAL CHARACTERISTIC CURVES

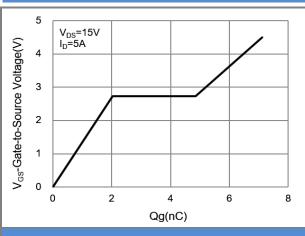


Fig.7 Gate-Charge Characteristics

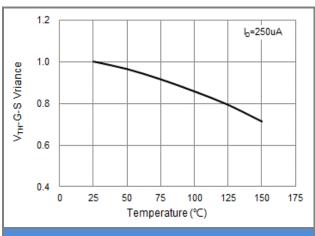


Fig.9 Threshold Voltage Variation with Temperature

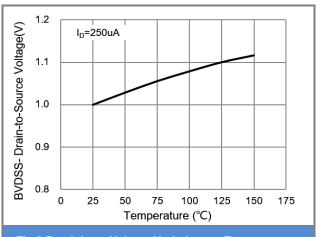


Fig.8 Breakdown Voltage Variation vs. Temperature

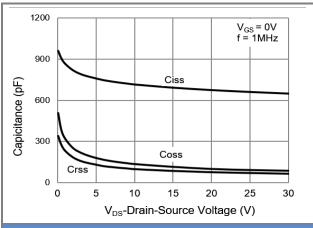


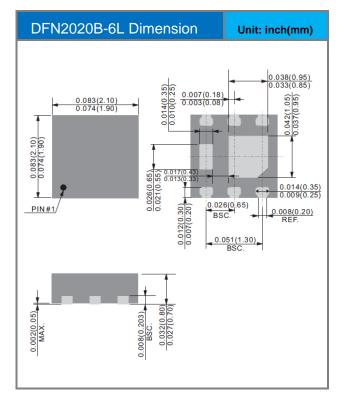
Fig.10 Capacitance vs. Drain-Source Voltage

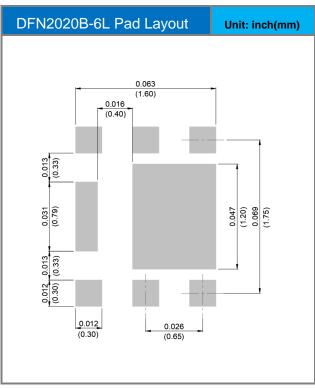


Product and Packing Information

| Part No. | Package Type | kage Type Packing Type | |
|------------|--------------|------------------------|-----|
| PJQ2410-AU | DFN2020B-6L | 3K pcs / 7" reel | 410 |

Packaging Information & Mounting Pad Layout







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